Si PIN Module

Features

Large Active diameter

Small dark current

High reliability

Applications

Fiberoptics telecommunication networks

Digital receivers

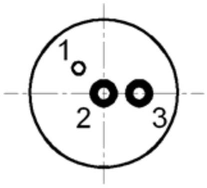
Optical interconnects

Test and measurement

Datacom

LAN

PIN assignment



pin	Function
1(case)	GND
2	N
3	P

This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures

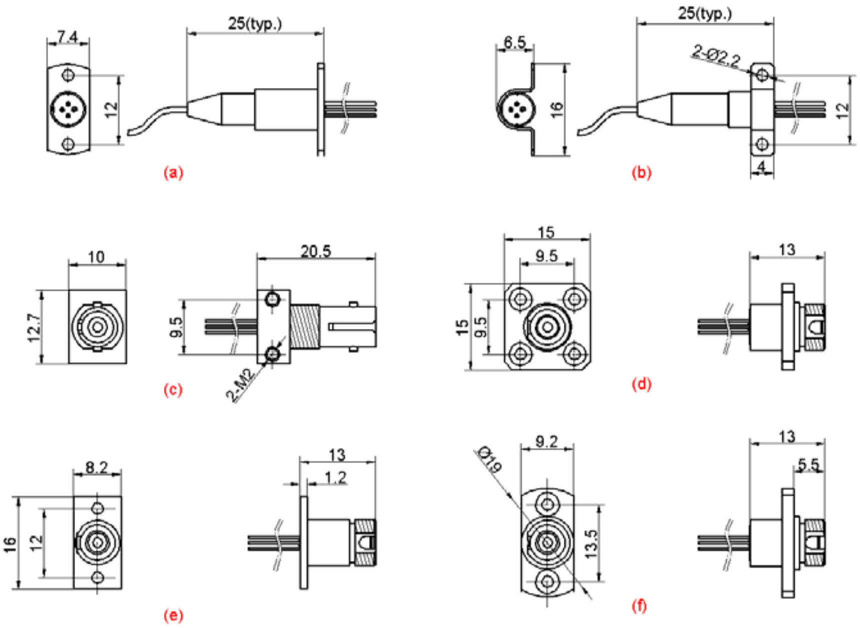
Absolute maximum ratings

Parameter	Symbol	Value	Unit
Storage temperature	Tst	-40~+85	°C
Operating temperature	Top	-40~+85	°C
Reverse voltage	V_R	30	V
Soldering temperature/time	—	260/10	°C/ s

Optical & electrical characteristics(T=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Detection range	λ	400	-	1100	nm	-
Dark current	I_d	-	-	10	nA	V_R=10mV
Quantum efficiency	R	-	0.4	-	A/W	V_R=10mV,λ=900 nm
Rise/fall time	Tr/f	-	1	3	ns	10%~90%
Capacitance	C_t	-	-	0.75	pF	V_R=10mV

Dimensions Diagram



Order information

SPD1	*X*	*X*
	Active area	**Package**
	1:0.5mm	1, (a)
	2:1mm	2, (b)
	3,2mm	3, (c)
		4, (d)
		5, (e)
		6, (f)
		S,spec.